

**AMENDMENTS TO THE SPECIFICATION**

**Please replace the first paragraph on page 1 with the following:**

This is a Continuation Application of U.S. Application No. 09/473,708 filed December 29, 1999, now U.S. Patent 6,719,842, claiming benefit pursuant to 35 U.S.C. § 119(e)(1) of the filing date of Provisional Application 60/114,376 filed December 30, 1998 pursuant to 35 U.S.C. § 111(b).

**Please replace the paragraph bridging pages 3 and 4 with the following:**

In the production of the GaN-type compound semiconductor device of Fig. 3 using the apparatus of Figs. 1 and 2, a sapphire substrate 1 is housed in a reactor 11, an organic gallium compound housed in a container 14 and an organic aluminum compound housed in a container 15 are bubbled with H<sub>2</sub> gas using tubes 21 and 22, the organic gallium compound gas and organic aluminum compound gas obtained are introduced together with H<sub>2</sub> gas into the reaction chamber 11 through inlet tubes 16 and 17, at the same time, ammonia gas supplied from a charging container 18 is introduced into the reaction chamber 11 through an inlet tube 19, and then a buffer layer 2 comprising Ga<sub>x</sub>Al<sub>1-x</sub>N is formed on the surface of the sapphire substrate 1 using these organic gallium compound gas, organic aluminum gas and ammonia compound gas as raw materials.